

#### CBM-XYTER Family Planning Workshop GSI December 10, 2008

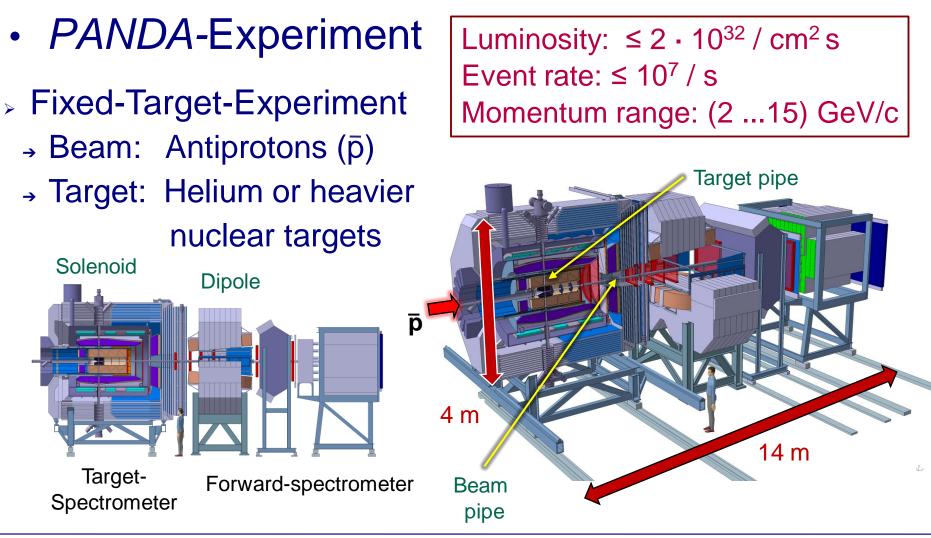
Thomas Würschig, Hans-Georg Zaunick

# Frontend electronics specifications for the silicon strip detectors of the PANDA MVD



# Introduction



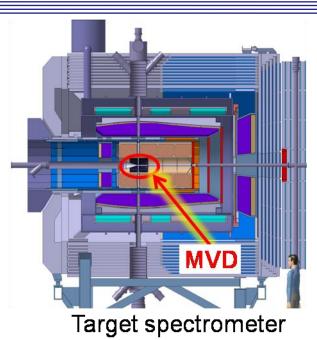


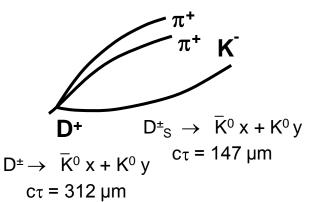


# Introduction



- Micro-Vertex-Detector (MVD)
  - a Tracking detector
  - b Innermost detector in PANDA
  - C High vertex resolution for primary interaction vertex as well as for secondary vertices of short living particles (e.g. mesons with charm and strange content) and delayed decay products
    - Should provide additionally some dE/dx information for PID



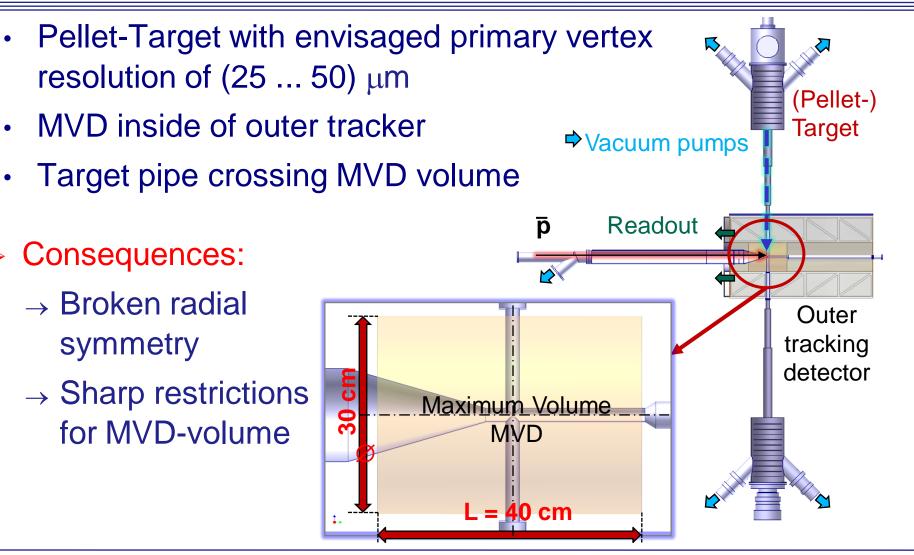




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# **Vertex-Geometry**

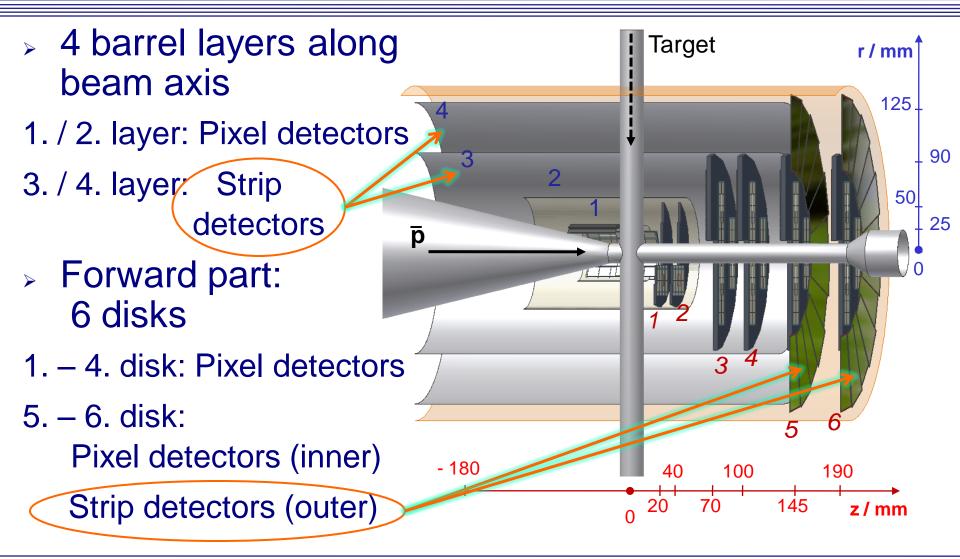






# **MVD Geometry**





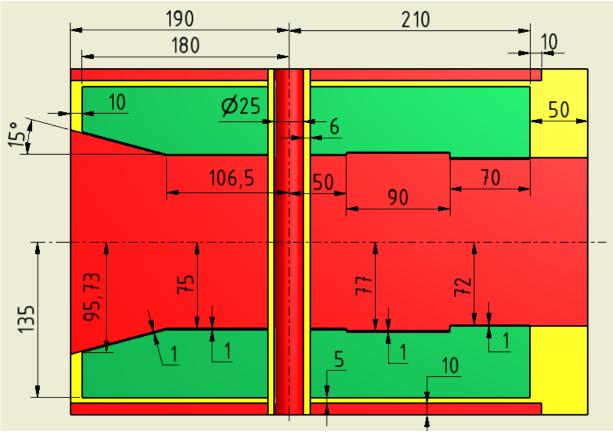


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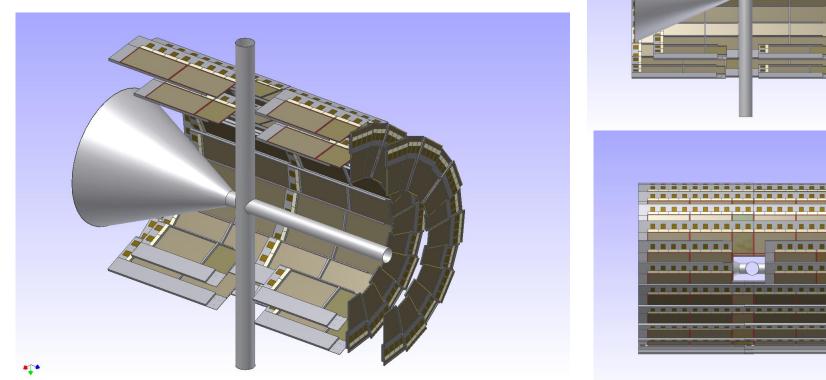
 Restricted volumes: Red (beam-target + pixel part) / Green (strip part) / Yellow (regions of interference)





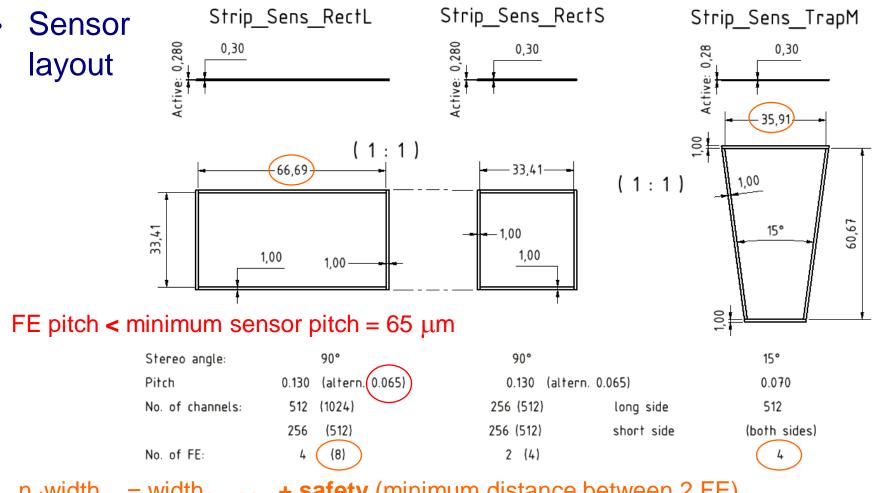


- Geometrical input
- Simulations of physics performance
- Feasibility for engineering process





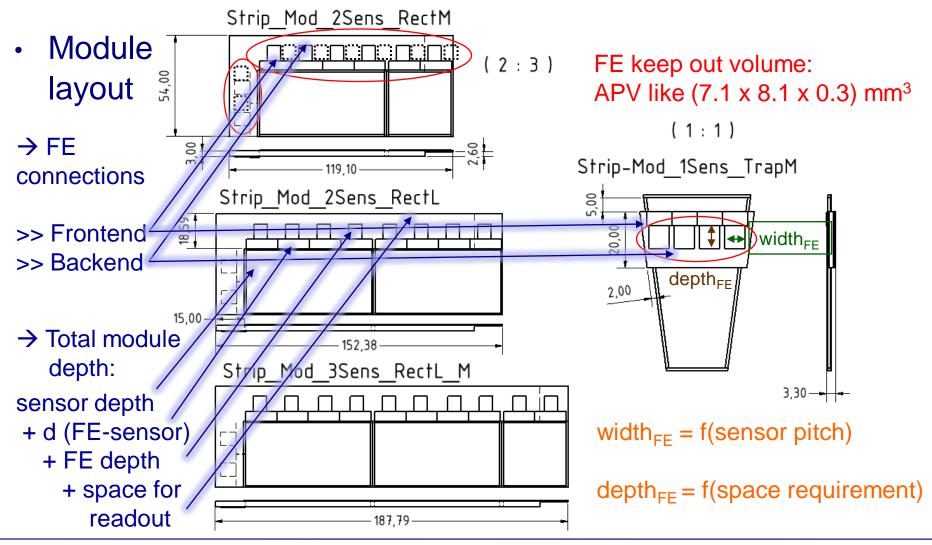




n .width<sub>FE</sub> = width<sub>SENSOR</sub> + safety (minimum distance between 2 FE)





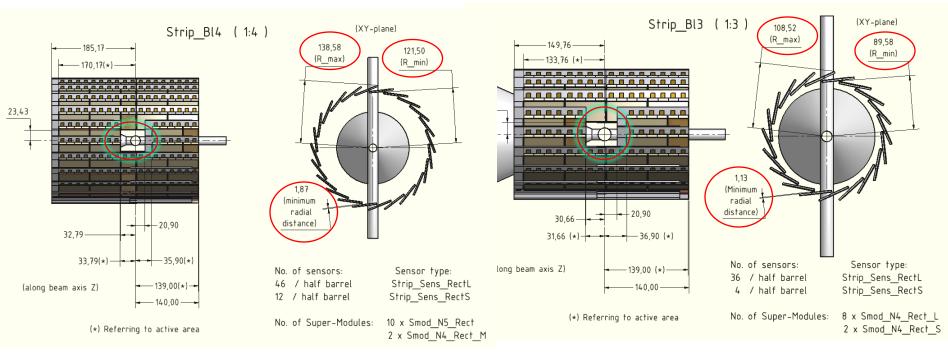




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Barrel layout



#### Impact of module sizes = f(sensor size; FE size)

#### Module depth <> space requirement: Inner + outer barrel radii / Minimum distances of super-modules / Keep out for target pipe

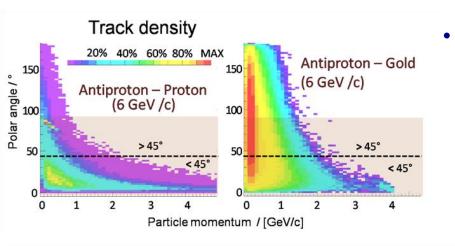


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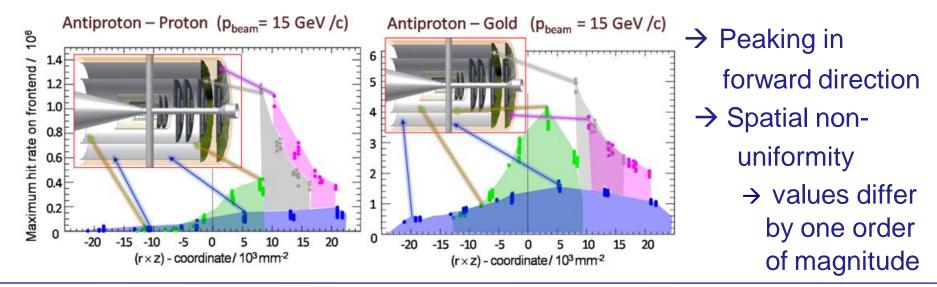
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## **Count rate studies**





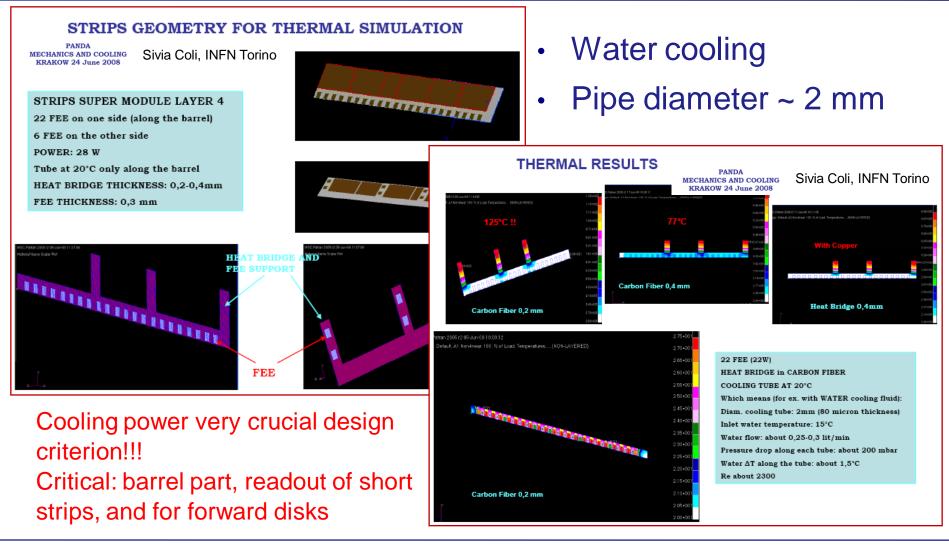
- Maximum hit rates at highest beam momenta assuming an interaction rate of 10<sup>7</sup> / sec:
  - $\rightarrow$  (1 ... 5) Mevts / sec / frontend
  - → Several 10k evts / sec / single channel





## Cooling

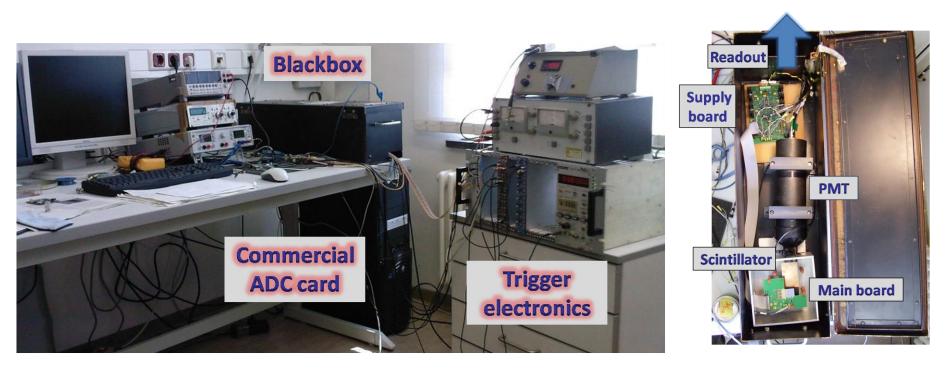








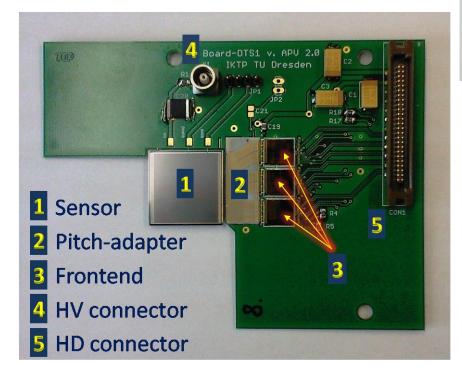
- Test station: DTS1 (Lab setup)
  - Evaluation of silicon strip sensors
  - Modular setup allowing further prototype testing

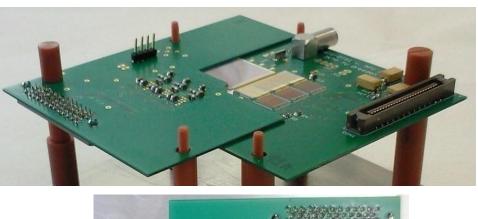


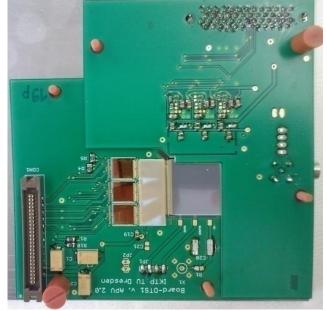




 Main sensor boards for double-sided readout



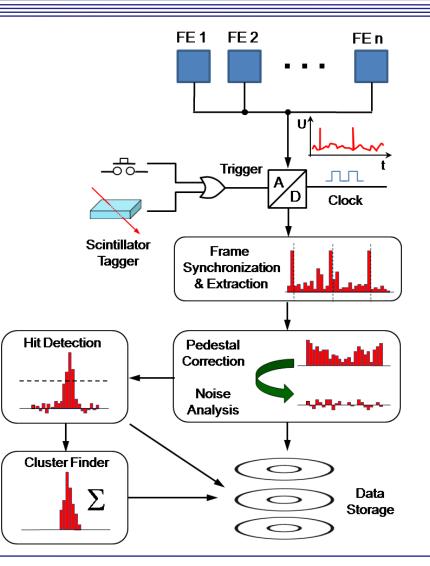








- Data acquisition (Lab-setup)
  - Used FE: APV25
  - Scintillation trigger
  - Feature extraction in software
  - Numerous tools to characterize module performance







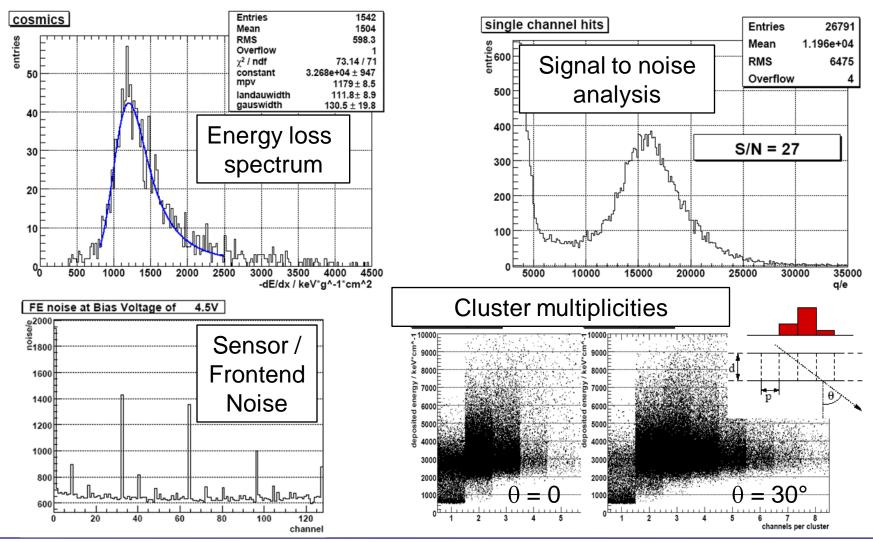
Test-beam setup in Bonn





#### **Measurements**



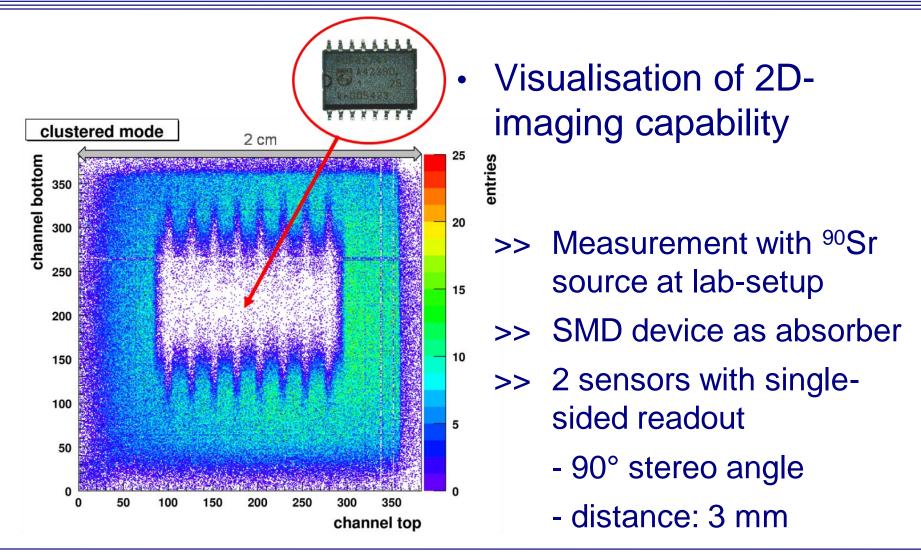




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#### Measurements







#### Database







# **FE requirements**



- Updated specifications based on:
  - Experimental setup
  - Physics requirements
  - Input of detailed implementation
    - Mechanics
    - Cooling
    - Support
    - Design optimisation:

technical feasibility <> detector simulations

Input of measurements with test station



## **FE requirements**



Parameter	Value	Remarks	
Geometry			
width	$\leq 8\mathrm{mm}$		
depth	$\leq 8\mathrm{mm}$		
input pad pitch	$\leq 50  \mu \mathrm{m}$		
		lateral pads occupied only for	
pad configuration		diagnostic functions, must be left	
		unconnected for final setup	
FE channels	$2^6 \dots 2^8$	default: 128 channels	
Input Compliance			
sensor capacitances, full depletion			
	< 10  pF	rect. short strips	
	< 50  pF	rect. long strips + ganging	
	$<\!20 \text{ pF}$	fw. disc strips	
charge polarity	either	selectable via slow control	
input ENC	$< 800  e^{-}$	$C_{Sensor} = 10 \mathrm{pF}$	
	$< 1100  e^-$	$C_{Sensor} = 25 \mathrm{pF}$	
Signal			
dynamic range	$160 \ ke^{-}$		
min. SNR for MIPs	12	$24.000 e^-$ MIPs in $300 \mu m$ Silicon,	
		guaranteed within lifetime	
peaking time	$pprox 1025\mathrm{ns}$	typical Si drift times	
digitization resolution	$\geq 8 \text{bit}$		





# **FE requirements**



Parameter	Value	Remarks	
Power			
overall power dissipation	< 1W	assuming 128 channels/FE	
Dynamical			
trigger	internally generated	when charge pulse exceeds	
		adjustable threshold level	
time stamp resolution	$<\!\!20ns$		
dead time / ch	${<}6\mu{ m s}$	baseline restored to within 1%	
		of equilibrium	
overshoot recovery time / ch	${<}25\mu{ m s}$		
average hit rates / ch		simulations $@$ 15 GeV beam mom.	
(poissonian mean)			
hot spots	$9.000 \ s^{-1}$	$\overline{p}p$	
	$40.000 \ s^{-1}$	$\overline{p}Au$	
average occupancy	$6.000 \ s^{-1}$	$\overline{p}p$	
	$30.000 \ s^{-1}$	$\overline{p}Au$	
Interface			
slow control	any		
data	sparsified digital		

Radiation Hardness: ~ 1Mrad (TID)

#### http://panda-wiki.gsi.de/cgi-bin/view/Mvd/FEspecs

